



Future Normal in Semiconductor

2025년 2월 13일(목), 15:50-17:20

Room C(컨벤션홀 L), 5층

D. Thin Film Process Technology 분과

029_[TC3-D] Emerging Devices - III

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<p>TC3-D-1 15:50-16:05</p>	<p>Atomic-Layer-Deposited Lithium Titanate-Based Artificial Synaptic Devices for Neuromorphic Computing Min Sub Kim, Hye Rim Kim, and Tae Joo Park Department of Materials Science and Chemical Engineering, Hanyang University</p>
<p>TC3-D-2 16:05-16:20</p>	<p>Synergistic Learning and Forgetting Effects for Optical and Electrical Stimulation in TiO₂-based Dual-Gate Dielectric Synaptic Transistors Youngbin Yoon¹, Jaehee Lee^{1,2}, and Jung Wook Lim^{1,2} ¹ETRI, ²UST</p>
<p>TC3-D-3 16:20-16:35</p>	<p>Implementation of Vertical-Channel Synapse Transistors Using an IGZO Active Layer with a Channel Length of 40 nm via HfO₂ Spacer Layer Nayoung Jang¹, Young Ha Kwon², Nak Jin Seong², Kyu Jeong Choi², and Sung Min Yoon¹ ¹Kyung Hee University, ²NCD Co. Ltd</p>
<p>TC3-D-4 16:35-16:50</p>	<p>Enhancement of Synaptic Characteristics and Spatiotemporal Processing in Electrolytic-Gated Synapse Transistors via a Gate Offset Geometry Hyunsik Woo and Sung-Min Yoon Kyung Hee University</p>
<p>TC3-D-5 16:50-17:05</p>	<p>All Transition Metal Dichalcogenides Based Wafer Scale 1T1R Array Via Crystallinity Engineering Hyunbin Choi¹, Hyunho Seok², Sihoon Son², Jinhyoung Lee³, and Taesung Kim^{1,2,3} ¹Department of Semiconductor Convergence Engineering, Sungkyunkwan University, ²SKKU Advance Institute of Nano Technology, ³Department of Mechanical Engineering, Sungkyunkwan University</p>